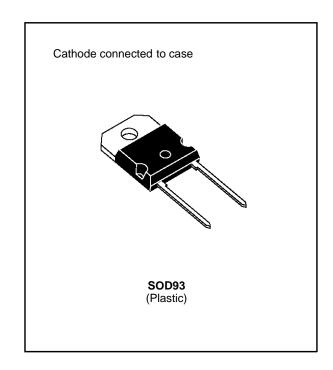


# **BYT 30P-1000**

# FAST RECOVERY RECTIFIER DIODE

- VERY HIGH REVERSE VOLTAGE CAPABILITY
- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING



#### **SUITABLE APPLICATIONS**

- FREE WHEELING DIODE IN CONVERTERS AND MOTOR CONTROL CIRCUITS
- RECTIFIER IN S.M.P.S.

#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage		1000	V
V <sub>RSM</sub>	Non Repetitive Peak Reverse Voltage		1000	V
I <sub>FRM</sub>	Repetive Peak Forward Current	t <sub>p</sub> ≤ 10μs	375	Α
I <sub>F (RMS)</sub>	RMS Forward Current	•	70	Α
I <sub>F (AV)</sub>	Average Forward Current	$T_c = 85^{\circ}C$ $\delta = 0.5$	30	А
I <sub>FSM</sub>	Surge non Repetitive Forward Current	t <sub>p</sub> = 10ms Sinusoidal	200	А
Р	Power Dissipation	T <sub>c</sub> = 85°C	60	W
T <sub>stg</sub> T <sub>j</sub>	Storage and Junction Temperature Range		- 40 to +150 - 40 to +150	°C

#### THERMAL RESISTANCE

Sym	bol	Parameter	Value	Unit
R <sub>th (j</sub>	(j - c)	Junction-case	1	°C/W

November 1994 1/5

#### **ELECTRICAL CHARACTERISTICS**

#### STATIC CHARACTERISTICS

Synbol		Min.	Тур.	Max.	Unit	
I <sub>R</sub>	T <sub>j</sub> = 25°C	$V_R = V_{RRM}$			100	μΑ
	T <sub>j</sub> = 100°C				5	mA
V <sub>F</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 30A			1.9	٧
	T <sub>j</sub> = 100°C				1.8	

#### RECOVERY CHARACTERISTICS

Symbol	Test Conditions					Тур.	Max.	Unit
t <sub>rr</sub>	T <sub>j</sub> = 25°C	I <sub>F</sub> = 1A	$di_F/dt = -15A/\mu s$	$V_R = 30V$			165	ns
		I <sub>F</sub> = 0.5A	I <sub>R</sub> = 1A	$I_{rr} = 0.25A$			70	

## TURN-OFF SWITCHING CHARACTERISTICS (Without Series Inductance)

Symbol		Min.	Тур.	Max.	Unit	
t <sub>IRM</sub>	di <sub>F</sub> /dt = - 120A/μs	V <sub>CC</sub> = 200 V I <sub>F</sub> = 30A			200	ns
	di <sub>F</sub> /dt = - 240A/μs	$L_p \le 0.05 \mu H$ $T_j = 100^{\circ} C$ See figure 11		120		
I <sub>RM</sub>	di <sub>F</sub> /dt = -120A/μs				19.5	А
	di <sub>F</sub> /dt = - 240A/μs			22		

### TURN-OFF OVERVOLTAGE COEFFICIENT (With Series Inductance)

Symbol	Test Condition s				Тур.	Max.	Unit
$C = \frac{V_{RP}}{V_{CC}}$	$T_j = 100^{\circ}C$ $di_F/dt = -30A/\mu s$	$V_{CC} = 200V$ $L_p = 5\mu H$	I <sub>F</sub> = I <sub>F (AV)</sub> See figure 12			4.5	

To evaluate the conduction losses use the following equation:

$$V_F = 1.47 + 0.010 I_F$$

$$P = 1.47 \text{ x } I_{F(AV)} + 0.010 I_{F}^{2}(RMS)$$

Figure 1. Low frequency power losses versus average current

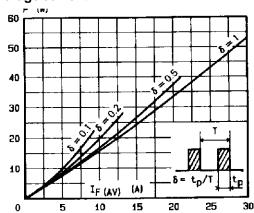


Figure 2. Peak current versus form factor

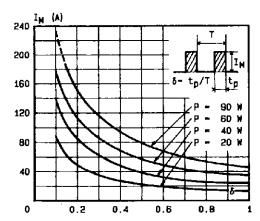


Figure 3. Non repetitive peak surge current versus overload duration

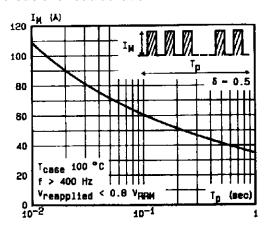


Figure 4. Thermal impedance versus pulse width

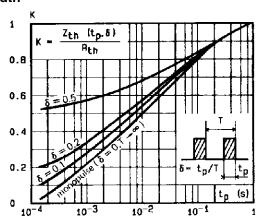


Figure 5. Voltage drop versus forward current

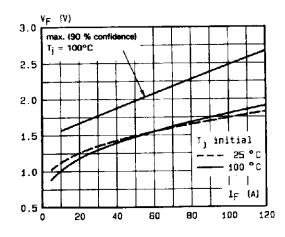


Figure 6. Recovery charge versus di<sub>F</sub>/d<sub>t-</sub>

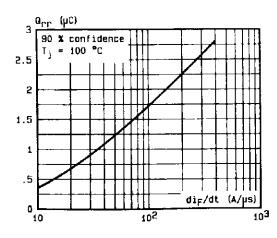


Figure 7. Recovery time versus di<sub>F</sub>/d<sub>t</sub>-

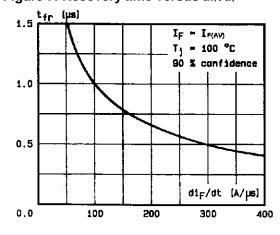


Figure 8. Peak reverse current versus dif/dt-

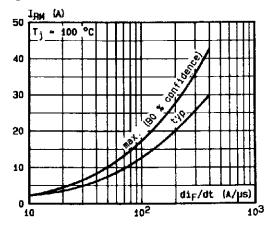


Figure 9. Peak forward voltage versus di<sub>F</sub>/d<sub>t-</sub>

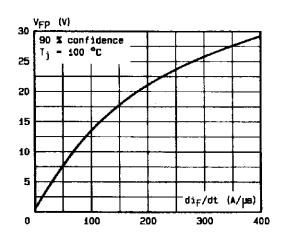


Figure 10. Dynamic parameters versus junction temperature.

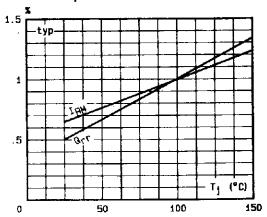


Figure 11. Turn-off switching characteristics (without series inductance).

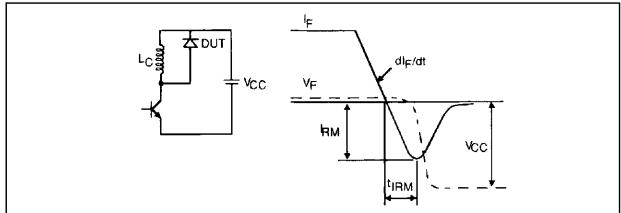
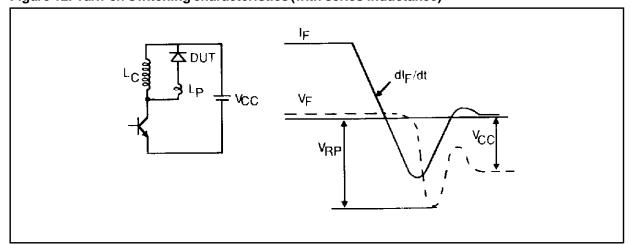
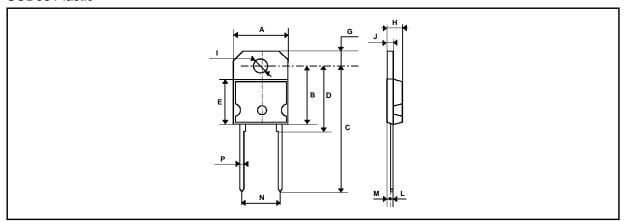


Figure 12. Turn-off switching characteristics (with series inductance)



#### **PACKAGE MECHANICAL DATA**

SOD93 Plastic



	DIMENSIONS					
REF.	Millimeters		Inc	hes		
	Min.	Max.	Min.	Max.		
Α	14.7	15.2	0.578	0.596		
В		16.2		0.637		
С	31 typ		1.220 typ			
D	18 typ		0.708 typ			
Е		12.2		0.480		
G	3.95	4.15	0.155	0.163		
Н	4.7	4.9	0.185	0.193		
I	4	4.1	0.157	0.161		
J	1.17	1.37	0.046	0.054		
L	0.5	0.78	0.019	0.030		
М	2.5 typ		0.098 typ			
N	10.8	11.1	0.425	0.437		
Р	1.1	1.3	0.043	0.051		

Cooling method: by conduction (method C) Marking: type number Weight: 4.3g

Recommended torque value: 80cm. N Maximum torque value: 100cm. N

Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsability for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectronics.

© 1994 SGS-THOMSON Microelectronics - Printed in Italy - All rights reserved.

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - United Kingdom - U.S.A.

